TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSII<sup>-5</sup>)

# 2SK1930

Chopper Regulator, DC–DC Converter, and Motor Drive Applications

- Low drain-source ON resistance  $: RDS (ON) = 3.0 \Omega (typ.)$
- High forward transfer admittance  $|Y_{fs}| = 2.0 \text{ S} (typ.)$
- Low leakage current  $: I_{DSS} = 300 \ \mu A \ (max) \ (V_{DS} = 800 \ V)$
- Enhancement mode  $: V_{th} = 1.5 \sim 3.5 \text{ V} (V_{DS} = 10 \text{ V}, \text{ ID} = 1 \text{ mA})$

#### Absolute Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	1000	V	
Drain-gate voltage (R	<sub>GS</sub> = 20 kΩ)	V <sub>DGR</sub>	1000	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	DC (Note 1)	۱ <sub>D</sub>	4	А	
	Pulse (Note 1)	I <sub>DP</sub>	12	~	
Drain power dissipation (Tc = 25°C)		PD	100	W	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

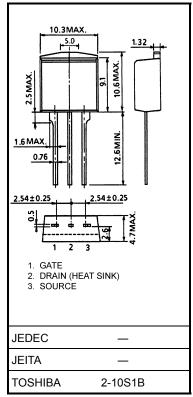
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

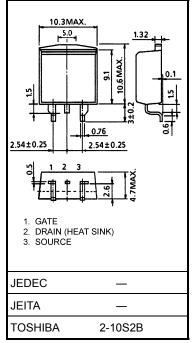
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R <sub>th (ch–c)</sub>	1.25	°C / W
Thermal resistance, channel to ambient	R <sub>th (ch–a)</sub>	83.3	°C / W

Note 1: Ensure that the channel temperature does not exceed 150°C.

This transistor is an electrostatic-sensitive device. Please handle with caution.



Weight: 1.5 g (typ.)



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Unit: mm

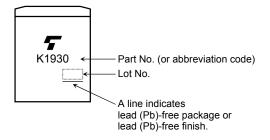
## **Electrical Characteristics (Ta = 25°C)**

Charao	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V	_	—	±100	nA
Drain cut-off cu	rrent	I <sub>DSS</sub>	V <sub>DS</sub> = 800 V, V <sub>GS</sub> = 0 V		_	300	μA
Drain-source br voltage	rain-source breakdown $V_{(BR) DSS}$ $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$		1000	_	_	V	
Gate threshold v	voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.5	_	3.5	V
Drain-source O	N resistance	R <sub>DS (ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2 A	_	3.0	3.8	Ω
Forward transfe	r admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 2 A	1.0	2.0	—	S
Input capacitance	ce	C <sub>iss</sub>		_	700	_	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz		55	_	pF
Output capacitance		C <sub>oss</sub>			100	_	
Switching time	Rise time	tr	$v_{GS} \stackrel{10V}{}_{0V} \prod_{U \\ C \\ $	_	18	_	- ns
	Turn-on time	t <sub>on</sub>		_	30	_	
	Fall time	t <sub>f</sub>		_	12	_	
	Turn-off time	toff	$V_{DD}$ ≒400V Duty ≦1%, t <sub>w</sub> =10µs	_	70	_	
Total gate charge (Gate-source plus gate-drain)		Qg		_	60	_	
Gate-source charge		Q <sub>gs</sub>	V <sub>DD</sub> ≈ 400 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4 A		35	_	nC
Gate-drain ("miller") charge		Q <sub>gd</sub>			25	_	

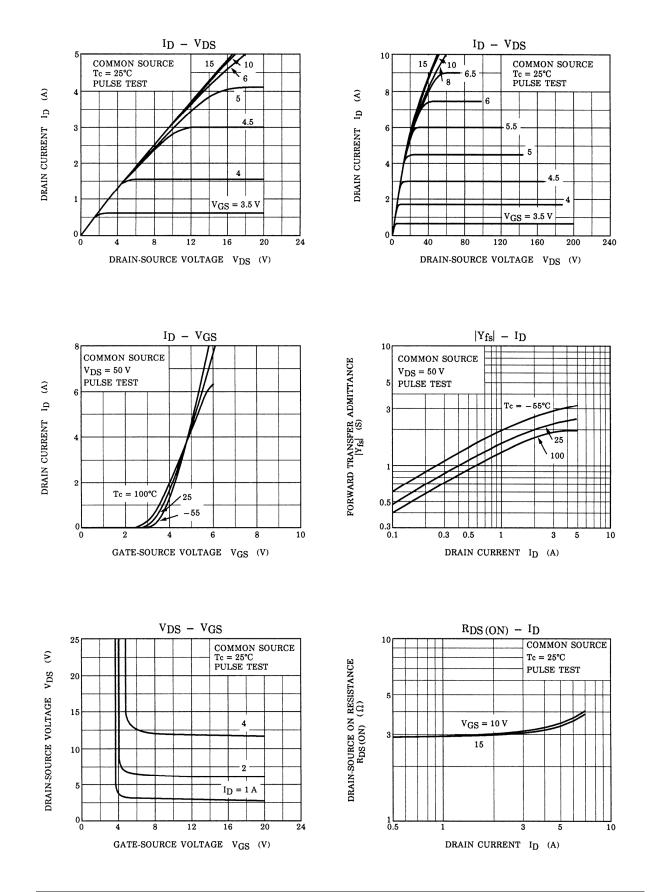
### Source–Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	_	_	_	4	А
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	—	_	_	12	A
Forward voltage (diode)	VDSF	I <sub>DR</sub> = 4 A, V <sub>GS</sub> = 0 V			-1.9	V

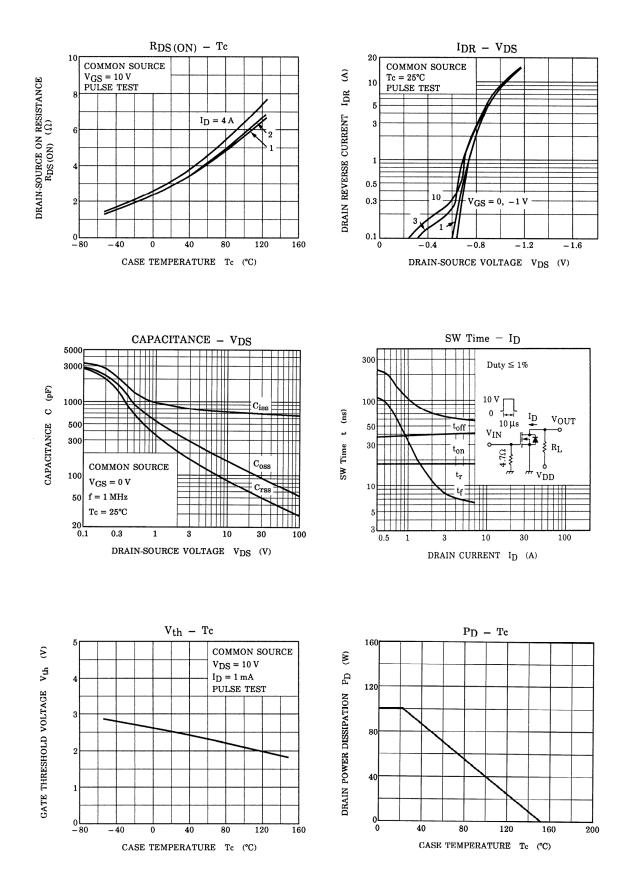
#### Marking

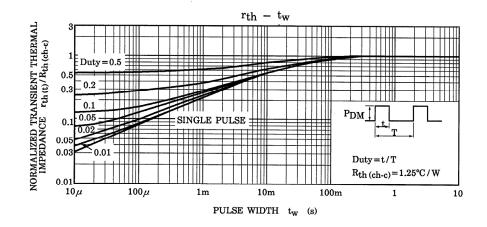


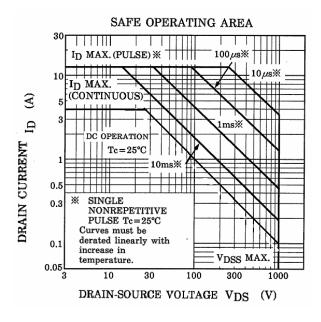
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